

Features:

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent

Switching

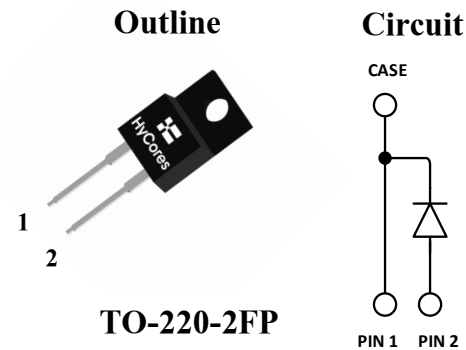
Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit
V_{RRM}	650	V
I_F ($T_C = 148^\circ\text{C}$)	6	A
Q_C	26	nC

Applications:

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters


Maximum Ratings

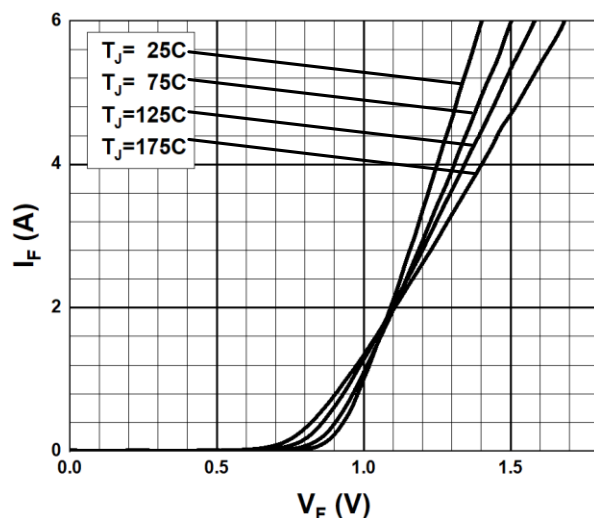
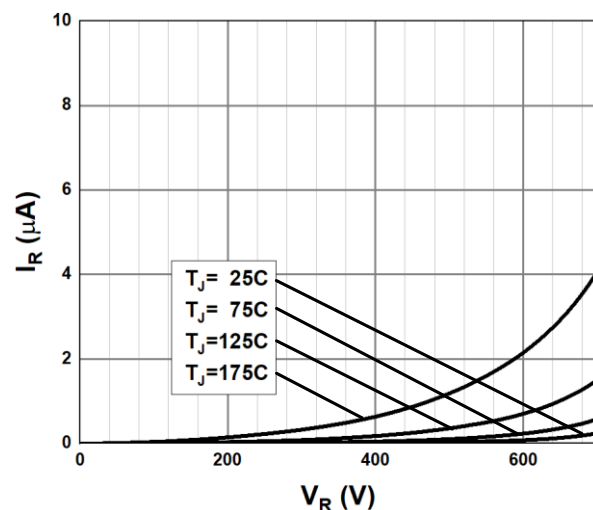
Symbol	Parameter	Value	Unit	Test Conditions
V_R	DC Peak Reverse Voltage	650	V	$T_J = 25^\circ\text{C}$
V_{RRM}	Repetitive Peak Reverse	650	V	$T_J = 25^\circ\text{C}$
V_{RSM}	Surge Peak Reverse Voltage	650	V	$T_J = 25^\circ\text{C}$
I_F	Continuous Forward Current	17.6	A	$T_C = 25^\circ\text{C}$
		8		$T_C = 135^\circ\text{C}$
		6		$T_C = 148^\circ\text{C}$
I_{FRM}	Repetitive Peak	51	A	$T_C = 25^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave
	Forward Surge Current	45		$T_C = 125^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave
I_{FSM}	Non-Repetitive Peak	66	A	$T_C = 25^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave
	Forward Surge Current	60		$T_C = 125^\circ\text{C}$, $T_p = 10\text{ms}$, Half Sine Wave
P_D	Power Dissipation	58.8	W	$T_C = 25^\circ\text{C}$
		19.6		$T_C = 125^\circ\text{C}$
$T_{J,max}$	Operating Junction Temperature	175	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$	

Thermal characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Thermal Resistance		2.55		$^{\circ}C/W$

Electrical Characteristics

Symbol	Parameter	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
V_{DC}	DC Blocking Voltage	650			V	$I_R = 100\mu A, T_J = 25^{\circ}C$
V_F	Forward Voltage		1.4 1.7	1.7 2.0	V	$I_F = 6A, T_J = 25^{\circ}C$ $I_F = 6A, T_J = 175^{\circ}C$
I_R	Reverse Current		1 10	30 100	μA	$V_R = 650V, T_J = 25^{\circ}C$ $V_R = 650V, T_J = 175^{\circ}C$
Q_C	Total Capacitive Charge		26		nC	$I_F = 6A, dI/dt = 400A/\mu s$ $T_J = 25^{\circ}C, V_R = 400V$
C	Total Capacitance		329 45 43		pF	$V_R = 1V, T_J = 25^{\circ}C, f = 1\text{ MHz}$ $V_R = 200V, T_J = 25^{\circ}C, f = 1\text{ MHz}$ $V_R = 400V, T_J = 25^{\circ}C, f = 1\text{ MHz}$

Typical Performance

Fig. 1 Forward Characteristics

Fig. 2 Reverse Characteristics

Typical Performance

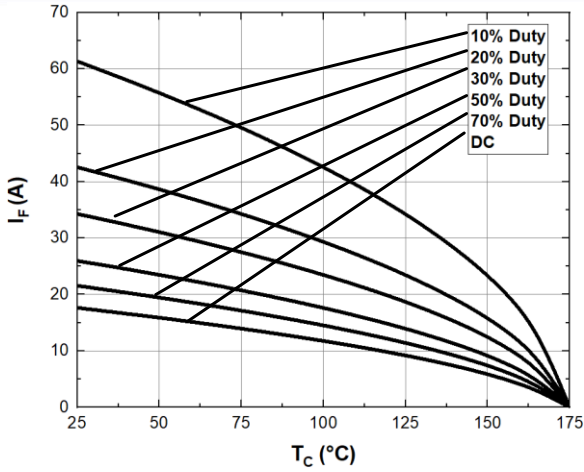


Fig. 3 Current Derating

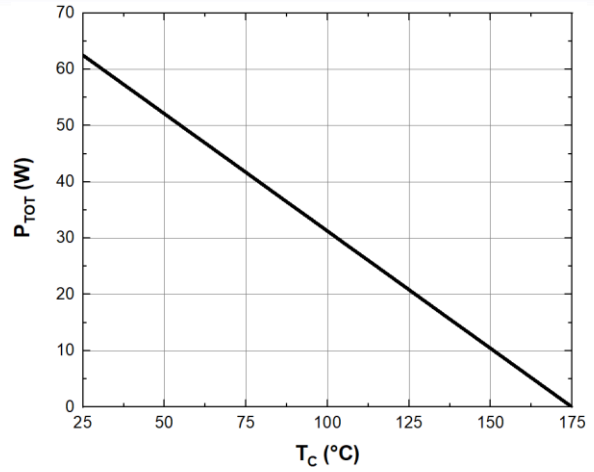


Fig. 4 Power Derating

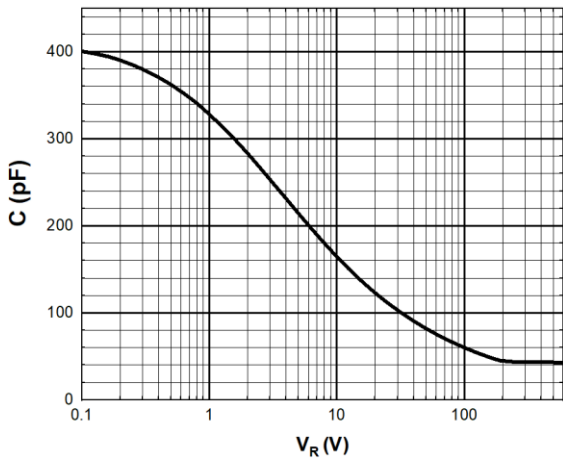


Fig. 5 Capacitance vs. Reverse Voltage

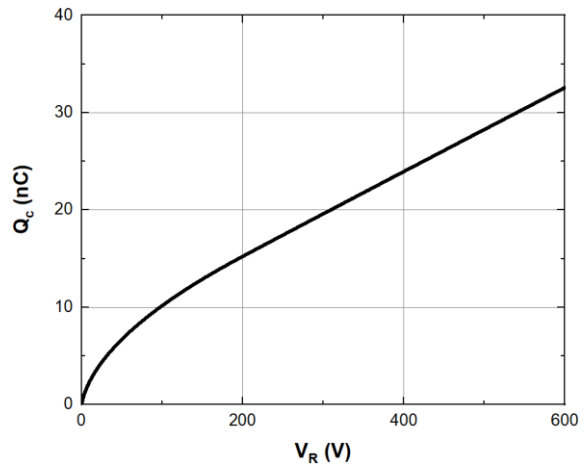


Fig. 6 Recovery Charge vs. Reverse Voltage

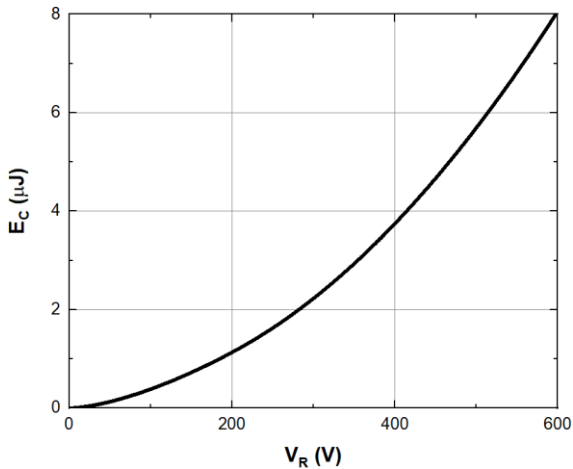


Fig. 7 Capacitance stored Energy

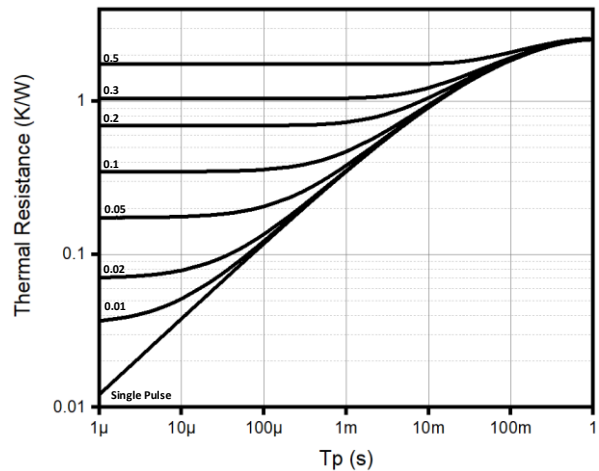
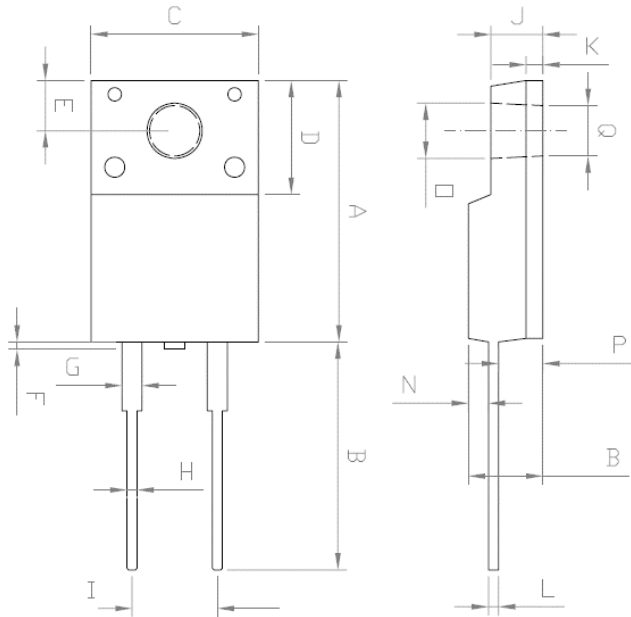


Fig. 8 Thermal Impedance

Package TO-220-2FP (Unit: mm)


REF.DIM	DATA BOOK mm		
	NOR	MIN	MAX
A	15.6	14.8	16.1
B	13	12.65	13.8
C	10	9.85	10.36
D	6.5	4.6	6.8
E	3.0	2.55	3.5
F			1
G	1.2	1	1.45
H	0.6	0.3	0.9
I	5.1	4.8	5.4
J	3.1	2.34	3.3
K	1.0	0.55	1.3
L	0.6	0.36	0.8
M	4.45	4.2	4.9
N	1.2	1.1	1.8
O	3.3	2.9	3.5
P	2.6	2.5	3.15
Q	3	2.9	3.5

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